I) Please amend the Specification as set forth below:

a) On page 1 line 30 to page 2, line 10, please amend the paragraph as set for below:

The dimension of such PDC is limited by many design rules. There is a design rule limiting the poly-to-diffusion distance (Dd-p), a design rule limiting the poly contact to diffusion distance (Dd-c), and a design rule limiting the contact to contact (Dc-c) distance as shown in FIG. 1(a). In the conventional techniques of integrated circuit designs, these design rules are originally required for the purpose of preventing accidental shorts between the poly and the diffusion areas. However, these design rules are still imposed and employed for designing IC circuits even under the circumstances that the circuit design is intended to connect the poly and diffusion areas. In the conventional techniques of IC design, these rules are still used even that those design rules are not meaningful as exemplified by a circuit as that shown in Fig. **1~~A~~(a)** and **1 ~~B~~(b).** In order to meet those design rules that are required for other purposes, current art PDC is highly inefficient. For many integrated circuits, especially for tightly pitched layout circuits, such limitations caused increase in overall layout area. It is therefore desirable to develop an efficient PDC structure to remove those constraints.

b) On page line 31 to page 5 line 4., please amend the paragraph as set forth below:

The above examples assume that the PDC contacts of the present invention are formed in the same time as other metal contacts for cost-saving reasons. It is certainly an option to use separated contact etching procedures specifically to form PDC contacts of the present invention. Using separated contact forming procedures will increase manufacture costs, but in will allow other options. One example is to use poly silicon as the contact filling materials (218, 258, <u>318</u> ~~358~~). It is also possible to further optimize the area of PDC contacts using separated manufacture procedures.